L Number	Hits	Search Text	DB	Time stamp
1	2	("6222225").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:08
2	5324	257/239,261,298,315-326.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:08
3	4472	438/201,211,216,241,257,258,260-266,591,593.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:10
4	9114	257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:10
5	1987	(257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near volatile near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:43
6	186	((257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat$3 oxide dielectric)) with (second near gate near (insulat$3 oxide dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:18
7	32	(((257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat$3 oxide dielectric)) with (second near gate near (insulat$3 oxide dielectric)))) and ((first near thick$4) with (second near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:14
8	68	((257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat$3 oxide dielectric)) with (second near gate near (insulat$3 oxide dielectric)) with thick$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:38
9	8	((257/239,261,298,315-326.ccls. 438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat$3 oxide dielectric) near thick$4) with (second near gate near (insulat$3 oxide dielectric) near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:43
10	349594	257/$.ccls. 438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:43
11	5004	(257/$.ccls. 438/$.ccls.) and (non near volatile near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:49
12	15	((257/$.ccls. 438/$.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat$3 oxide dielectric) near thick$4) with (second near gate near (insulat$3 oxide dielectric) near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:49
13	3	("4471373" | "5194924" | "5237188").PN.	USPAT	2004/07/20 11:47

14	60231	non near volatile near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:49
15	16	(non near volatile near memory) and ((first near gate near (insulat$3 oxide dielectric) near thick$4) with (second near gate near (insulat$3 oxide dielectric) near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:55
16	44	((first near gate near (insulat$3 oxide dielectric) near thick$4) with (greater bigger larger) with (second near gate near (insulat$3 oxide dielectric) near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:52
17	179	((first near gate near (insulat$3 oxide dielectric) near thick$4) with (second near gate near (insulat$3 oxide dielectric) near thick$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:55